OK TO ENTER: /A.S./

IFW AF



## N THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

Valerie BOUSQUET, et al.

Conf. No.:

7512

Application No.:

10/525,499

Examiner:

Asok K. SARKAR

August 19, 2009

371(c) Date:

September 21, 2005

Art Unit:

2891

Title:

MBE GROWTH OF A SEMICONDUCTOR LAYER STRUCTURE

Atty. Dkt. No.:

24500-000015/US

Customer Service Window Randolph Building 401 Dulany Street Alexandria, VA 22314

**Mail Stop AF** 

## AMENDMENT UNDER 37 C.F.R. § 1.116

## Sir/Madam:

In response to the Final Office Action mailed May 22, 2009, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

Amendments to the Claims begin on page 2 of this paper.

**Remarks** begin on page 4 of this paper.

	Claims remaining after Amendment		Highest number previously paid for		Present extra
Total	4	-	20	=	0
Independent	1	_	3	=	0